

BSS84

P-channel enhancement mode vertical DMOS transistor Rev. 06 — 16 December 2008 Product data

Product data sheet

1. Product profile

1.1 General description

P-channel enhancement mode vertical Diffusion Metal-Oxide Semiconductor (DMOS) transistor in a small Surface-Mounted Device (SMD) plastic package.

Table 1. Product overview

Type number[1]	Package	
	NXP	JEDEC
BSS84	SOT23	TO-236AB
BSS84/DG		

^{[1] /}DG: halogen-free

1.2 Features

Low threshold voltage

High-speed switching

Direct interface to CMOS and Transistor-Transistor Logic (TTL)

No secondary breakdown

1.3 Applications

■ Line current interrupter in telephone sets ■ Relay, high-speed and line transformer drivers

1.4 Quick reference data

 $V_{DS} \le -50 \text{ V}$

 \blacksquare R_{DSon} \leq 10 Ω

 $I_D \le -130 \text{ mA}$

Arr P_{tot} \leq 250 mW



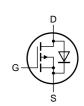
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Pinning information 2.

2

Table 2. **Pinning** Pin **Symbol Description** Simplified outline 1 G gate





001aaa025

2 of 11

Graphic symbol

Ordering information 3.

Table 3. **Ordering information**

Type number[1]	Package		
	Name	Description	Version
BSS84	TO-236AB	plastic surface-mounted package; 3 leads	SOT23
BSS84/DG			

^{[1] /}DG: halogen-free

Marking

Product data sheet

Table 4. **Marking codes**

Type number[1]	Marking code ^[2]
BSS84	13*
BSS84/DG	ZV*

^{[1] /}DG: halogen-free

[2] * = -: made in Hong Kong

* = p: made in Hong Kong

* = t: made in Malaysia

* = W: made in China

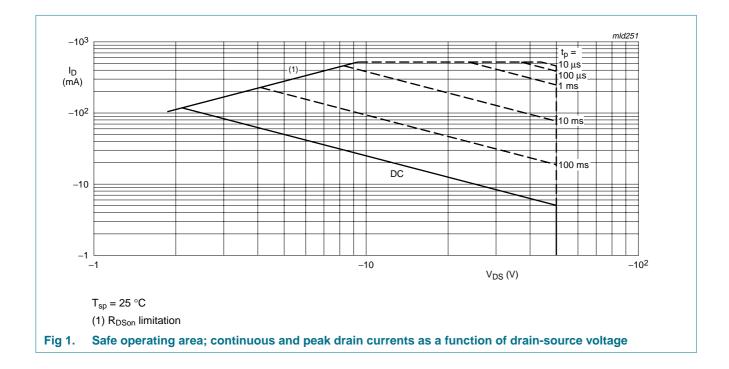
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5. Limiting values

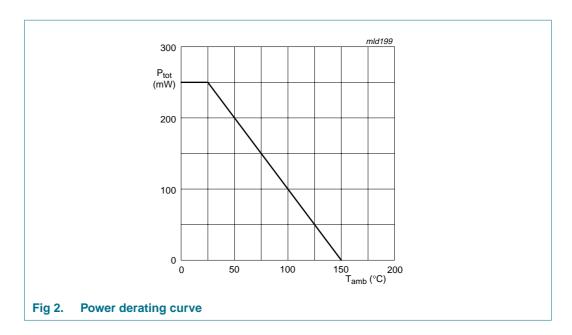
Table 5. Limiting values
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$25~^{\circ}C \le T_j \le 150~^{\circ}C$	-	-50	V
V_{GS}	gate-source voltage		-	±20	V
I _D drain current	$T_{sp} = 25 ^{\circ}\text{C}; V_{GS} = -10 \text{V};$ see Figure 1	-	-130	mA	
		T _{sp} = 100 °C; V _{GS} = -10 V	-	-75	mA
I _{DM}	peak drain current	T_{sp} = 25 °C; $t_p \le 10 \mu s$; see <u>Figure 1</u>	-	-520	mA
P _{tot}	total power dissipation	T _{sp} = 25 °C; see <u>Figure 2</u>	[1] -	250	mW
T _{stg}	storage temperature		-65	+150	°C
T _i	junction temperature		-65	+150	°C

^[1] Device mounted on a Printed-Circuit Board (PCB).



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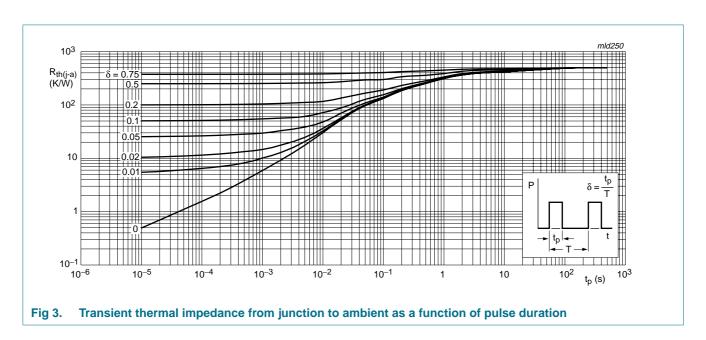


6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	see Figure 3	[1] -	-	500	K/W

[1] Mounted on a PCB, vertical in still air.



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7. Characteristics

Table 7. Characteristics

 $T_i = 25 \,^{\circ}C$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -10 \ \mu A; \ V_{GS} = 0 \ V$	-50	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = -1 \text{ mA}; V_{DS} = V_{GS};$ see Figure 8				
		T _j = 25 °C	-0.8	-	-2	V
		T _j = −55 °C	-	-	-1.8	V
I _{DSS}	drain leakage current	$V_{DS} = -40 \text{ V}; V_{GS} = 0 \text{ V}$				
		T _j = 25 °C	-	-	-100	nΑ
		$V_{DS} = -50 \text{ V}; V_{GS} = 0 \text{ V}$				
		T _j = 25 °C	-	-	-10	μΑ
		T _j = 125 °C	-	-	-60	μΑ
I _{GSS} gate	gate leakage current	$V_{GS} = +20 \text{ V}; V_{DS} = 0 \text{ V}$	-	-	100	nΑ
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}$	-	-	100	nΑ
R _{DSon}	drain-source on-state resistance	$V_{GS} = -10 \text{ V};$ $I_D = -130 \text{ mA};$ see Figure 5 and 7	-	6	10	Ω
Dynamic o	characteristics					
Y _{fs}	transfer admittance	$V_{DS} = -25 \text{ V};$ $I_D = -130 \text{ mA}$	50	-	-	mS
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = -25 \text{ V};$	-	25	45	pF
Coss	output capacitance	f = 1 MHz; see Figure 9	-	15	25	pF
C _{rss}	reverse transfer capacitance		-	3.5	12	pF
t _{on}	turn-on time	$V_{DS} = -40 \text{ V}; V_{GS} = 0 \text{ V}$ to -10 V; $I_{D} = -200 \text{ mA};$ see <u>Figure 10</u> and <u>11</u>	-	3	-	ns
t _{off}	turn-off time	$V_{DS} = -40 \text{ V};$ $V_{GS} = -10 \text{ V to 0 V};$ $I_D = -200 \text{ mA};$ see Figure 10 and 11	-	7	-	ns

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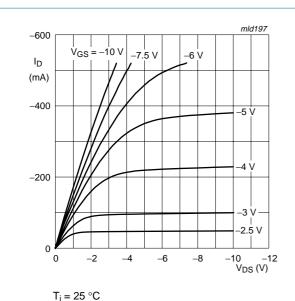
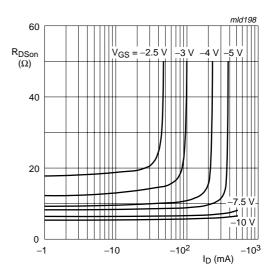


Fig 4. Output characteristics: drain current as a function of drain-source voltage; typical values



T_j = 25 °C

Fig 5. Drain-source on-state resistance as a function of drain current; typical values

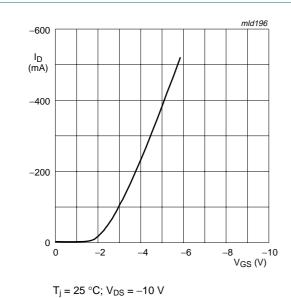
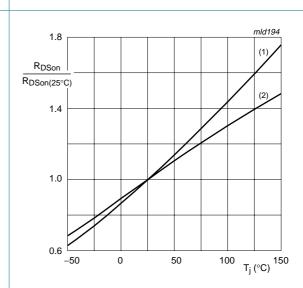


Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values



(1) $I_D = -130 \text{ mA}$; $V_{GS} = -10 \text{ V}$ (2) $I_D = -20 \text{ mA}$; $V_{GS} = -2.4 \text{ V}$

Fig 7. Normalized drain-source on-state resistance factor as a function of junction temperature

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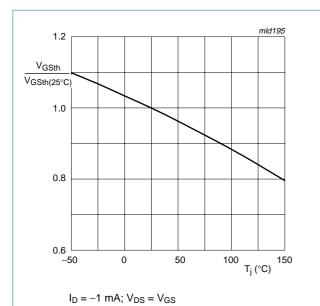
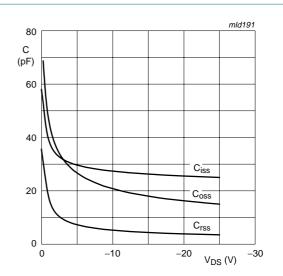


Fig 8. Gate-source threshold voltage as a function of junction temperature



 $V_{GS} = 0 V$; f = 1 MHz

Fig 9. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

8. Test information

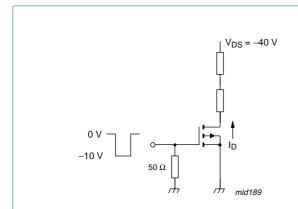


Fig 10. Switching time test circuit

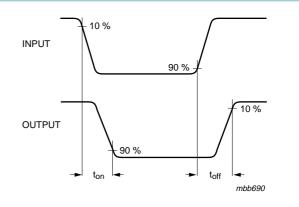


Fig 11. Input and output waveforms

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9. Package outline

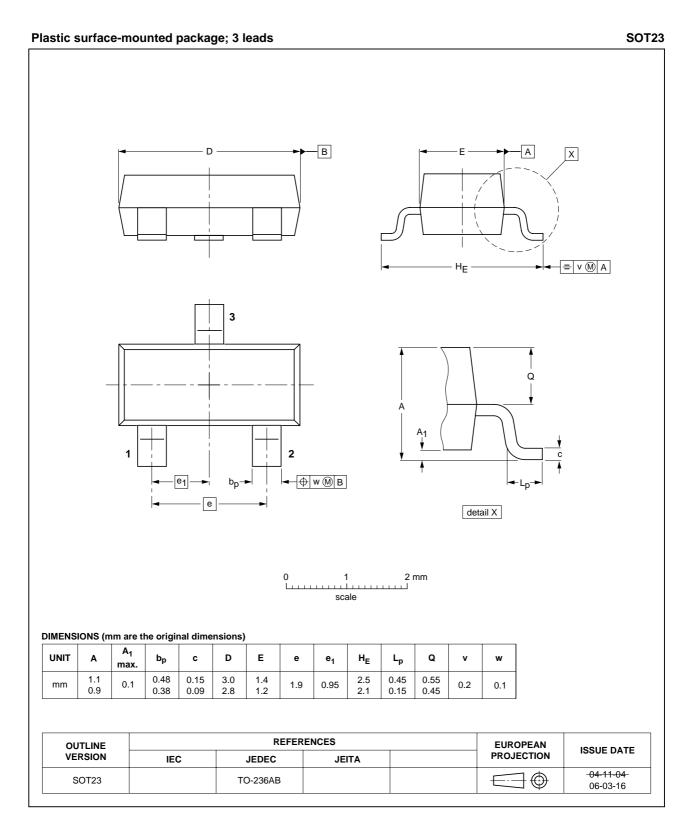


Fig 12. Package outline SOT23 (TO-236AB)

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10. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BSS84_6	20081216	Product data sheet	-	BSS84_5
Modifications:	 Table 5 "Limit 	ing values": P _{tot} figure referen	ce updated	
BSS84_5	20081209	Product data sheet	-	BSS84_4
BSS84_4	20070717	Product data sheet	-	BSS84_3
BSS84_3	20030804	Product specification	-	BSS84_2
BSS84_2	19970618	Product specification	-	BSS84_1
BSS84_1	19950407	Product specification	-	-

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11. Legal information

11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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